

1 Claim 4 (amended):

2 The device according to claim 3, wherein the substrate can be maintained at elevated
3 temperatures during transition from MOVPE to HVPE.

1 Claim 5 (amended):

2 The device according to claim 2, wherein said device can also transition from HVPE to
3 MOVPE *in situ*.

1 Claim 6 (amended): The device according to claim 5, wherein said device can also

2 transition from HVPE to MOVPE *in situ*.

1 Claim 7 (amended):

2 The device according to claim 6, wherein the substrate can be maintained at elevated
3 temperatures during transition from HVPE to MOVPE.

1 Claim 8 (amended):

2 The device according to claim 1, wherein said device can be used to grow a
3 III-V nitride compound semiconductor onto the surface of the substrate.

1 Claim 9 (amended): The device according to claim 8, wherein said device can be used

2 to grow GaN onto the surface of the substrate.

1 Claim 10 (amended):

2 The device according to claim 9, wherein said means for performing HVPE comprises
3 a hot wall reactor having a source zone, and

4 a downstream mixing zone,

5 wherein TMG can be reached with Hcl in the source zone to form a chlorinated ^Ggallium
6 species, and wherein the chlorinated ^Ggallium species can combine with NH₃ in the downstream
7 mixing zone and directed toward the substrate for deposition of GaN onto the substrate.

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Docket No. UF-222XC2D2

Serial No. 09/735,217

- A/Conclude*
- OK*
- 1 Claim 11 (amended):
 - 2 The device according to claim 9, wherein said means for performing MOVPE comprises
 - 3 a low pressure ~~horizontal~~ cold-wall MOCVD reactor.

horizontal
